TENTATIVE

Nihon Inter Electronics Corporation

SBD MODULE 80A/150V

P2H80QH15

OUTLINE DRAWING

See the Next Page

FEATURES

* Compatible with Isolated Base SOT227
* Dual Separated Diodes
* Extremely Low Forward Voltage Drop
* Low Power Loss, High Efficiency
* High Surge Capability

TYPICAL APPLICATIONS

* High Frequency Rectification

Maximum Ratings

Approx Net Weight:35g

Parameter	Symbol	Type / Grade		Unit
		P2H80QH15	-	
Repetitive Peak Reverse Voltage *1	V_{RRM}	150	-	V
Non Repetitive Peak Reverse Voltage *1	V_{RSM}	-	-	

Parameter			Conditions	Max Rated Value	Unit
Average Rectified Output Current *1		$I_{O(AV)}$	50Hz Half Sine Wave condition Tc=To Be Determined	80	A
Surge Forward Current *1		I_{FSM}	50 Hz Half Sine Wave,1Pulse Non-repetitive	800	A
Operating JunctionTemperature Range		Tjw		-40 to +150	℃
Storage Temperature Range		Tstg		-40 to +125	℃
Isoration Voltage		Viso	Base Plate to Terminals, AC1min	2500	V
Mounting torque	Terminals	Ftor	M4Screw	1.5(1.4)	N•m
	Case mounting		M4Screw with Thermal Compound	1.5(1.4)	

Electrical • Thermal Characteristics

Characteristics	Symbol	Test Conditions	Max.	Unit
Peak Reverse Current *1	I_{RM}	V_{RM}= V_{RRM}, Tj= 25℃	60	μA
Peak Forward Voltage *1	V_{FM}	I_{FM}= 80A, Tj=25℃	1.02	V
Thermal Resistance *1	Rth(j-c)	Junction to Case	0.53	℃/W
	Rth(c-f)	Base Plate to Heat Sink with Thermal Compound	0.3	

*1: Value Per 1Arm

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P2H80QH15 OUTLINE DRAWING (Dimensions in mm)